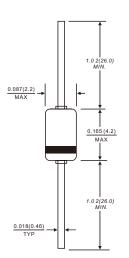
# 1N4148

### **SMALL SIGNAL SWITCHING DIODE**

#### DO-35(GLASS)



### **FEATURES**

- Silicon epitaxial planar diode
- Switching diodes
- 500mw power dissipation
- High temperature soldering guaranteed 250 °C/10 seconds,0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

### **MECHANICAL DATA**

Case: DO-35 glass sealed envelope. Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026 Polarity: Color band denotes cathode end Mounting Position: Any Weight: 0.005 ounce, 0.14 grams(DO-35)

Dimensions in inches and (millimeters)

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specialized. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

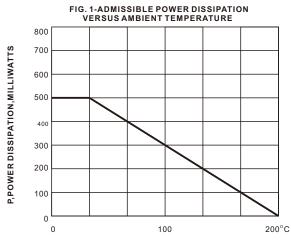
	SYMBOLS	1N4148	UNITS
Maximum repetitive peak reverse voltage	VRRM	100	VOLTS
Maximum RMS voltage	VRMS	75	VOLTS
Maximum average forward rectified current 0.375"(9.5mm) lead length at T <b>A</b> =25 °C	I(AV)	150	mAmps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	500	mAmps
Maximum instantaneous forward voltage at 10mA	VF	1.0	Volts
Maximum DC reverse current TA=25°C VR=75V at rated DC blocking voltage TA=100°C VR=20V	IR	5.0	mA
Maximum reverse recovery time (NOTE 1)	trr	4.0	ns
Typical junction capacitance (NOTE 2)	CJ	4.0	pF
Operating junction and storage temperature range	TJ,TSTG	-60 to +200	°C

NOTES:1.Test condition:IF=10mA,IR=10mA,Irr=1mA,VR=6V,RL=100Ω.

NOTES:2.Measured at 1.0 MHz and applied reverse voltage of 4.0 volts 1.Test condition:IF=10mA,IR=10mA,Irr=1mA,VR=6V,RL=100W.

2.Measured at 1.0 MHz and applied reverse voltage of 4.0 volts

## **RATINGS AND CHARACTERISTIC CURVES 1N4148**





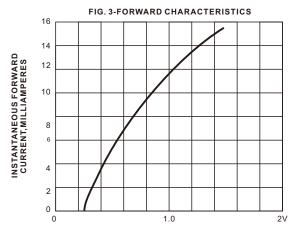
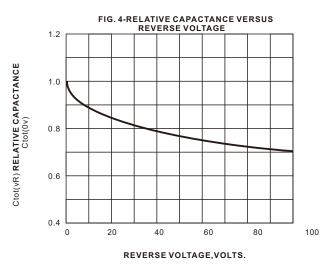
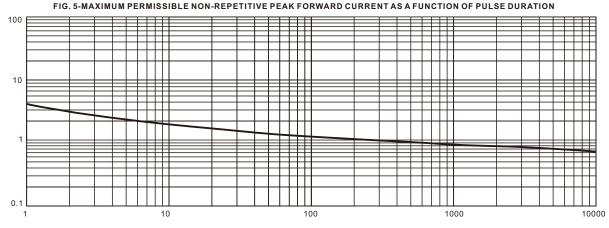




FIG. 2-REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE (TYPICAL VALUES)







Based on square wave currents. Tj=25\* prior to surge.

